

# HiPerFET™ Power MOSFET

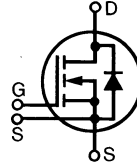
Single MOSFET Die

Preliminary data sheet

IXFE 24N100  
IXFE 23N100

$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
1000 V	22 A	0.39 $\Omega$
1000 V	21 A	0.43 $\Omega$

$t_{rr} \leq 250$  ns

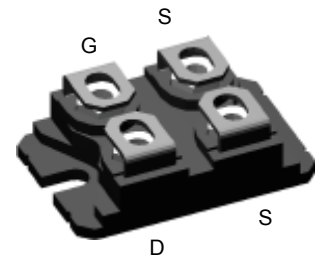


## Symbol Test Conditions

## Maximum Ratings

$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1000	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1\text{M}\Omega$	1000	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	24N100: 22 23N100: 21	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ ; Note 1	24N100: 96 23N100: 92	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	24	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	60	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	3	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100$ A/ $\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$ , $R_G = 2 \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	500	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ min $I_{ISOL} \leq 1$ mA $t = 1$ s	2500 3000	V~ V~
$M_d$	Mounting torque Terminal connection torque	1.5/13 Nm/lb.in. 1.5/13 Nm/lb.in.	
<b>Weight</b>		19	g

## ISOPLUS 227™ (IXFE)



G = Gate  
S = Source  
D = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

## Features

- Conforms to SOT-227B outline
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

## Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

## Advantages

- Low cost
- Easy to mount
- Space savings
- High power density

## Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

## Characteristic Values

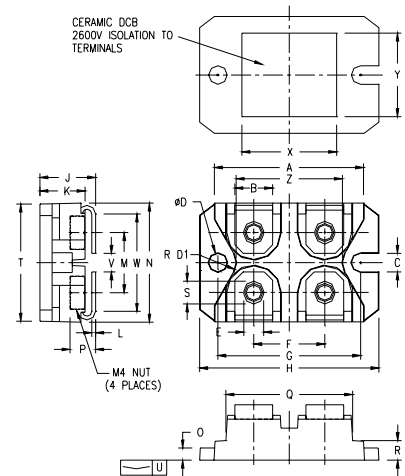
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0$ V, $I_D = 3$ mA	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8$ mA	3.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 20$ V, $V_{DS} = 0$ V			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		100 $\mu\text{A}$ 2 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = I_T$ Note 2	23N100 24N100		0.43 $\Omega$ 0.39 $\Omega$

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$				
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = I_T, \text{ Note 2}$	15	22	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		7000	pF
$C_{oss}$			750	pF
$C_{rss}$			260	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ $R_G = 1\ \Omega \text{ (External)}$		35	ns
$t_r$			35	ns
$t_{d(off)}$			75	ns
$t_f$			21	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$		250	nC
$Q_{gs}$			55	nC
$Q_{gd}$			135	nC
$R_{thJC}$			0.25	K/W
$R_{thCK}$			0.07	K/W

**Source-Drain Diode**
 $(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$ 

Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
$I_S$	$V_{GS} = 0$	24N100 23N100		24 23	A A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$	24N100 23N100		96 92	A A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5	V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		1.0	250	ns
$Q_{RM}$					$\mu\text{C}$
$I_{RM}$			8		A

- Notes:
1. Pulse width limited by  $T_{JM}$ .
  2. Pulse test,  $t \leq 300\text{ ms}$ , duty cycle  $d \leq 2\%$ .
  3.  $I_T$  Test current:  
24N100:  $I_T = 12\text{ A}$   
23N100:  $I_T = 11.5\text{ A}$

**ISOPLUS-227 B**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.270	31.50	32.26
B	.310	.330	7.87	8.38
C	.155	.165	3.94	4.19
D	.155	.165	3.94	4.19
D1	.150	.157	3.81	3.98
E	.160	.168	4.06	4.27
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.489	1.505	37.80	38.23
J	.465	.481	11.81	12.22
K	.370	.380	9.40	9.65
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.100	.105	2.54	2.67
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.160	.170	4.06	4.32
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.001	.002	-0.03	0.05
V	.130	.160	3.30	4.06
W	.780	.830	19.81	21.08
X	.770	.810	19.56	20.57
Y	.680	.720	17.27	18.29
Z	.885	.892	22.48	22.66

Please see IXFN24N100 data sheet for characteristic curves.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	